

F16.5

FORMING STEP OF RESIN FILM /FORMING STEP OF CONTACT HOLE / FORMING STEP OF PIXEL ELECTRODE

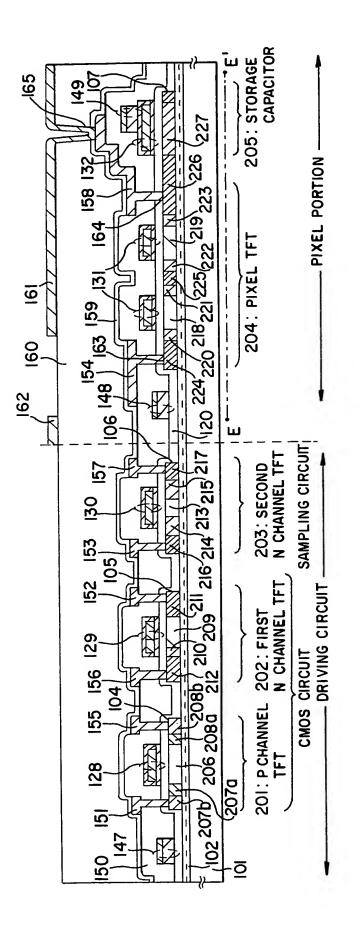


FIG.6(A)

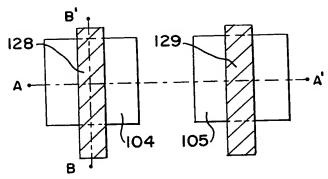


FIG.6(B)

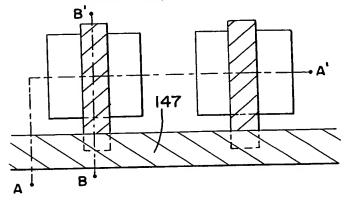


FIG.6(C)

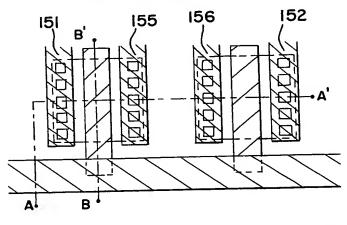


FIG. 7(A)

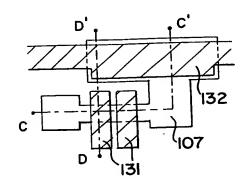


FIG.7(B)

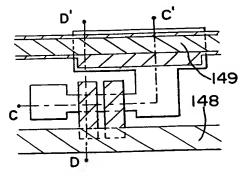
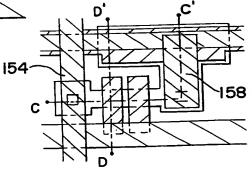


FIG. 7(C)



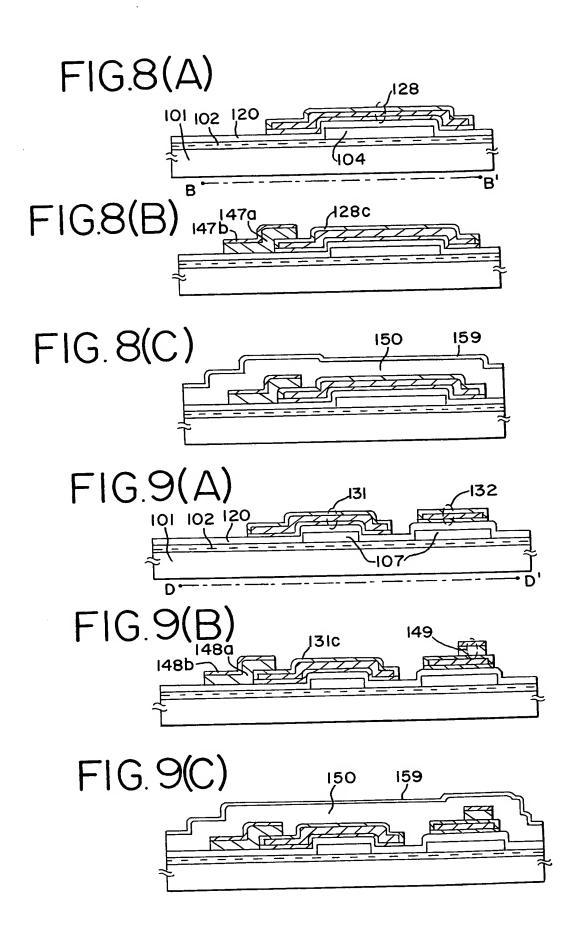
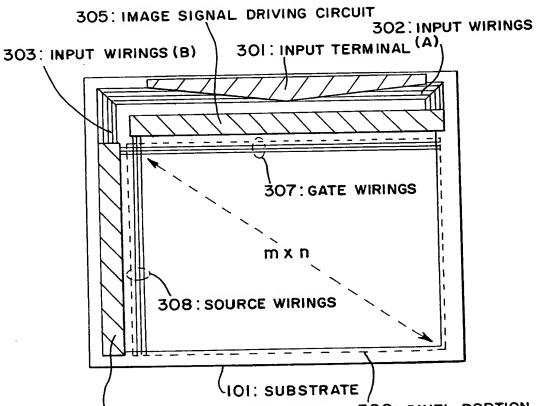
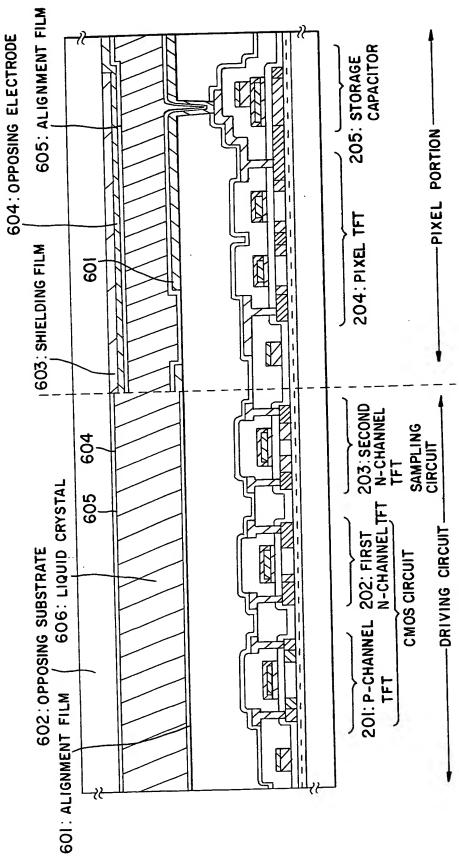


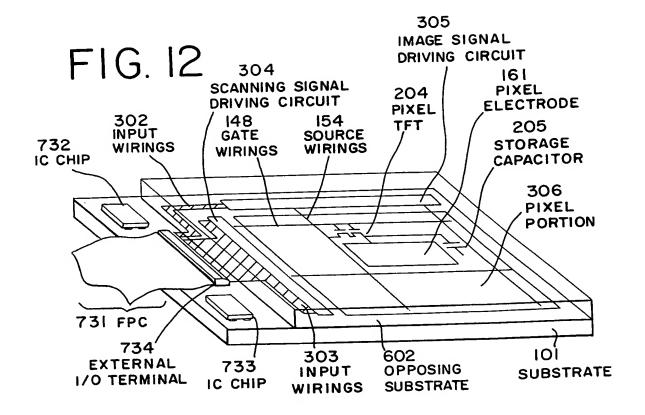
FIG.10



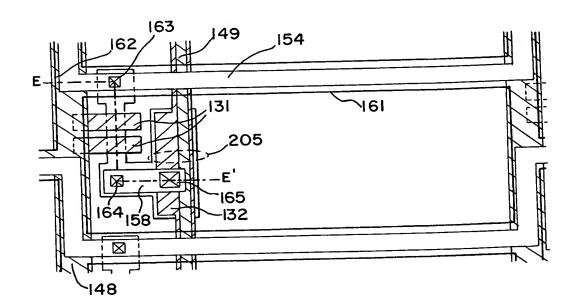
304: SCANNING SIGNAL DRIVING CIRCUIT 306: PIXEL PORTION

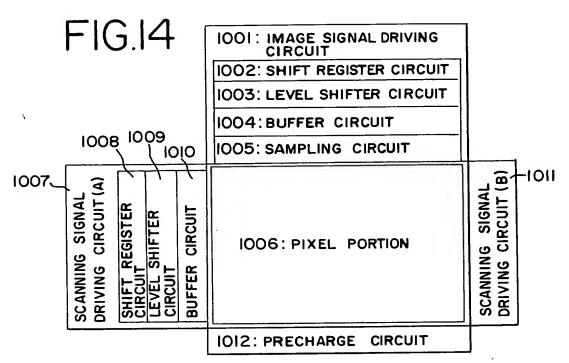
FIG.II

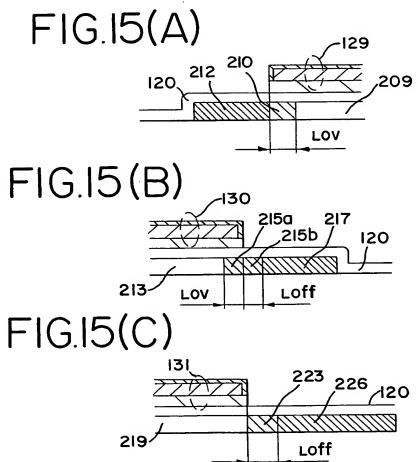


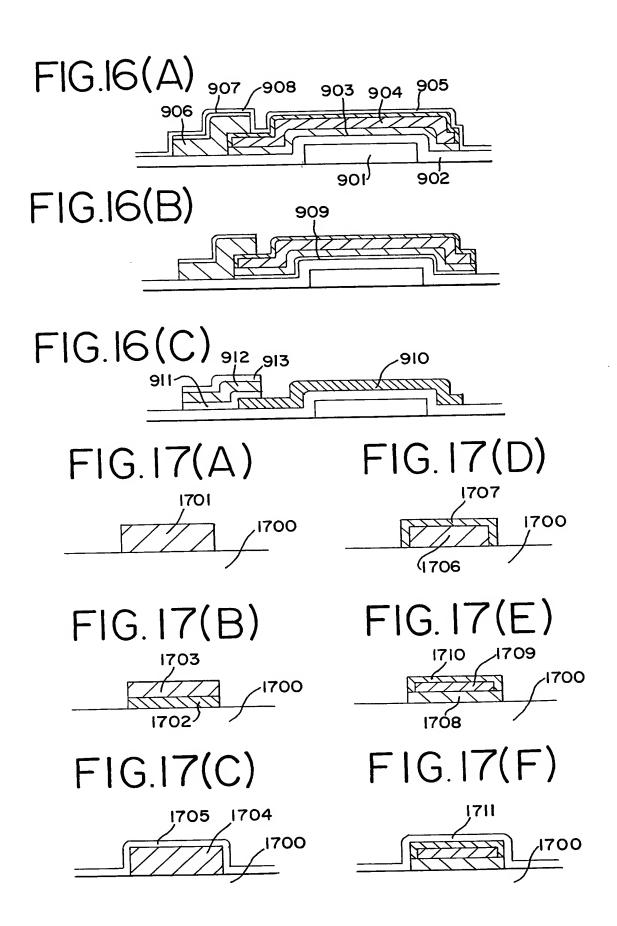


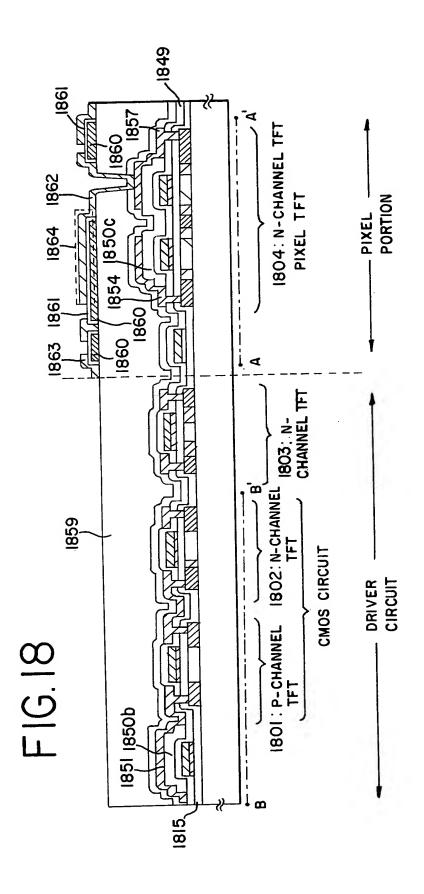
F1G. 13

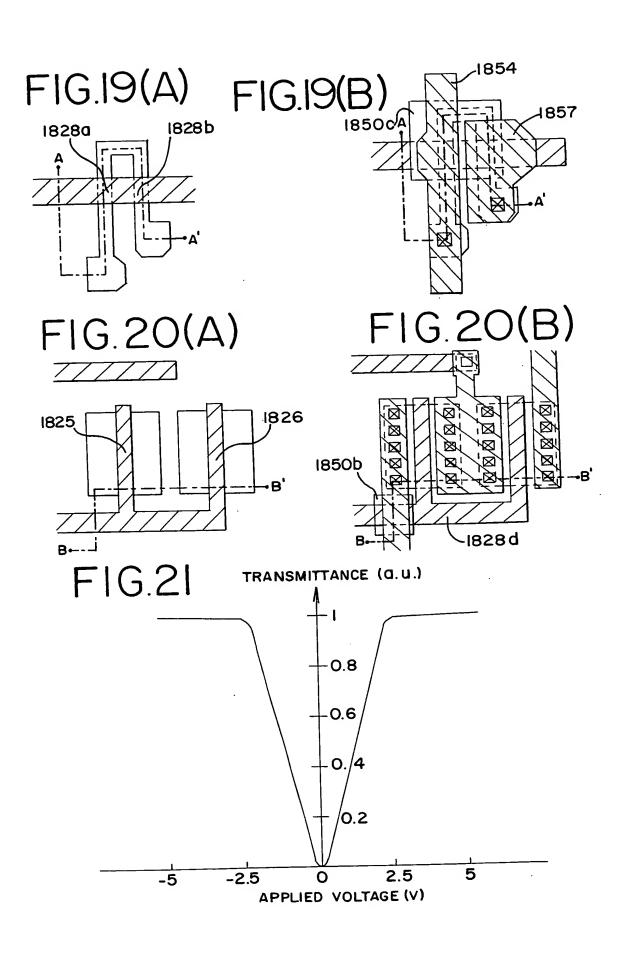












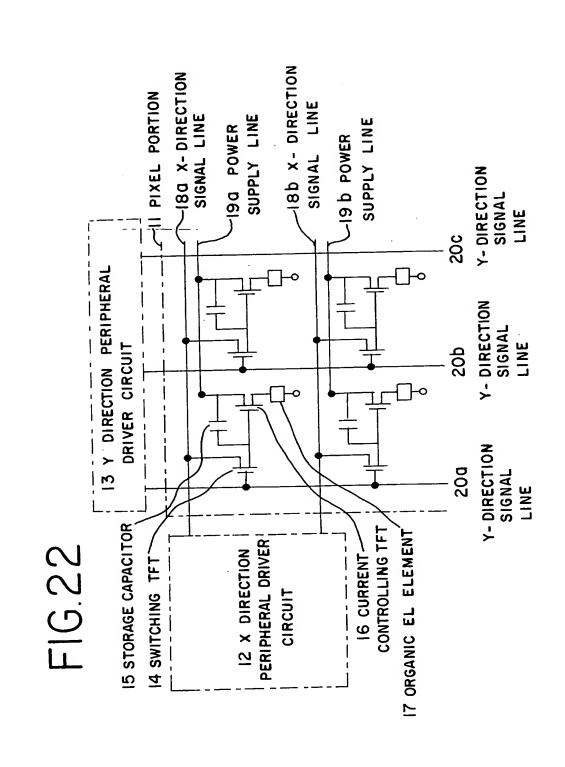


FIG. 23(B) FIG.23(A) 2106 IMAGE RECEIVING 2001 MAIN BODY SEÇTION 2002 IMAGE INPUT SECTION 2101 MAIN 2104 BODY **OPERATION** 2103 VOICE 2003 DISPLAY SECTION SWITCHES INPUT 品。 SECTION 2004 KEYBOARD 41/1**%**11 2102 DISPLAY SECTION 2105 BATTERY FIG.23(C) FIG.23(D) 2201 MAIN BODY 2205 DISPLAY / SECTION 2202 CAMERA SECTION 2301 2003 ARM SECTIONS MAIN 2203. IMAGE BODY RECEIVING SECTION 2204 OPERATION SWITCHES FIG. 23(E) 2302 DISPLAY SECTION 2402 DISPLAY SECTION FIG.23(F) 2401 MAIN BODY 2504 2503 **OPERATION** VIEW FINDER SWITCHES 2501 MAIN 2403 BODY **SPEAKER** SECTION 2404 RECORDING MEDIUM 2502 2405 DISPLAY **OPERATION**

SWITCHES

SECTION

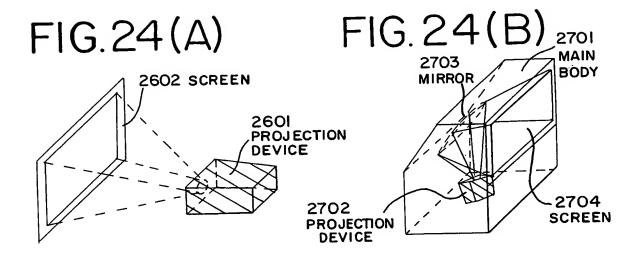


FIG. 24(C) PROJECTION DEVICE (THREE-PLATE STYLE)
TOWARD SCREEN

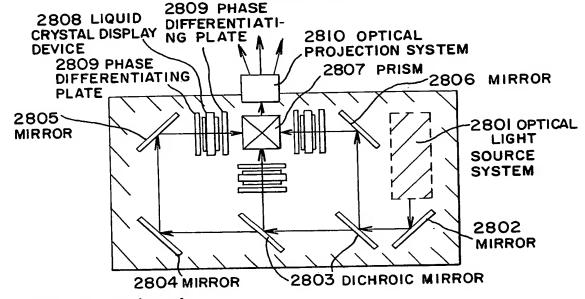
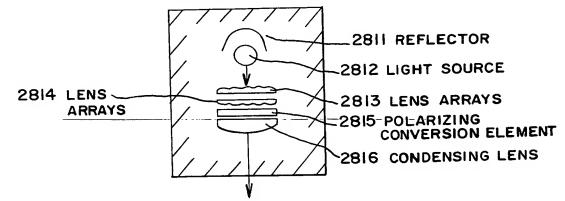
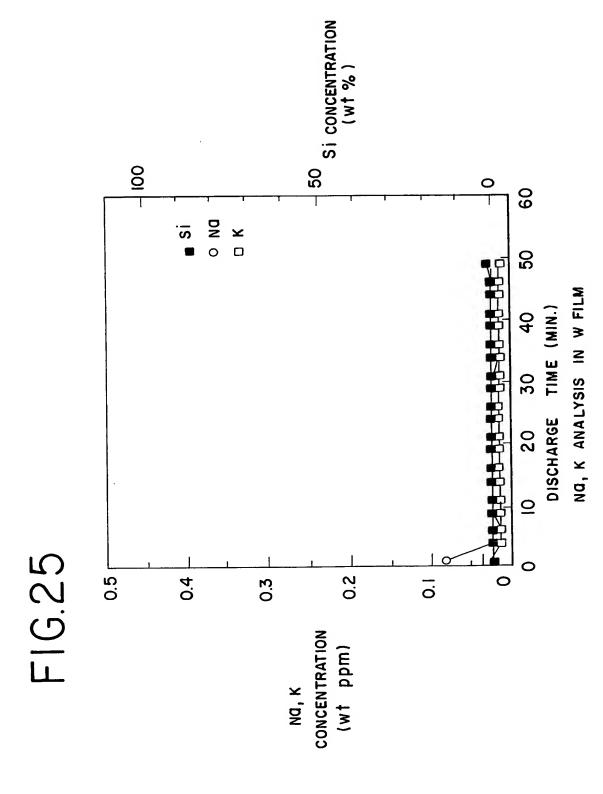


FIG. 24(D) OPTICAL LIGHT SOURCE SYSTEM





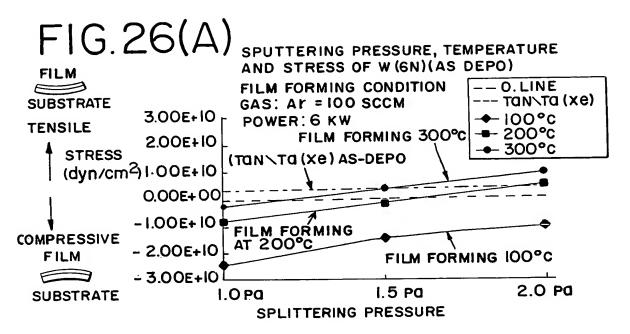


FIG. 26(B) SPUTTERING PRESSURE AND STRESS OF W (6N)

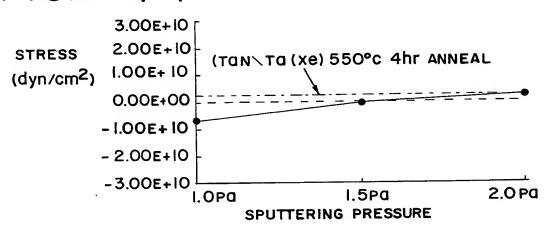


FIG. 26(C) SPUTTERING PRESSURE AND STRESS OF W (6N) (800°C 1 hr ANNEAL)

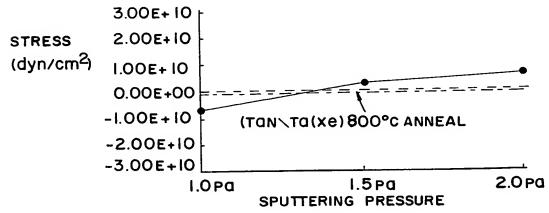


FIG.27(A) SPUTTERING PRESSURE, TEMPERATURE, AND RESISTIVITY OF W (6N) (AS-DEPO) 25 FILM FORMING -100°C CONDITION -200°c 20 100°C GAS: Ar=100SSCM -300℃ POWER: 6KW 15 RESISTIVITY (hJcm) 10 2008 300°c 5 0 2.0 Pa I.OPa 1.5 Pa SPUTTERING PRESSURE FIG.27(1 SPUTTERING PRESSURE AND RESISTIVITY WHERE W (6N) IS FORMED AT 200°C (500°C 4hr ANNEAL) 25 20 15 RESISTIVITY -w(6N)200°C 10 (m \(\mathcal{L} \) cm) 5 0 2.0 Pa I.Opa 1.5Pa SPUTTERING **PRESSURE** FIG.27(C) SPUTTERING PRESSURE AND RESISTIVITY OF W (6N) (800°C Ihr ANNEAL) 25 20 15 RESISTIVITY - W(6N)200°C 10 (µ \(\Om\) 5 1.5 Pa 2.0 Pa I.OPa

SPUTTERING PRESSURE

FIG. 28(A) TENSILE STRESS

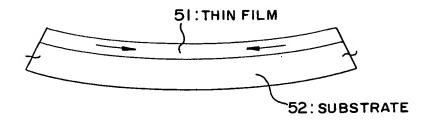


FIG.28(B)

COMPRESSIVE STRESS

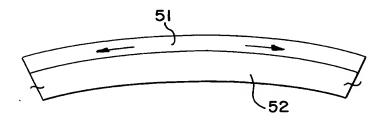


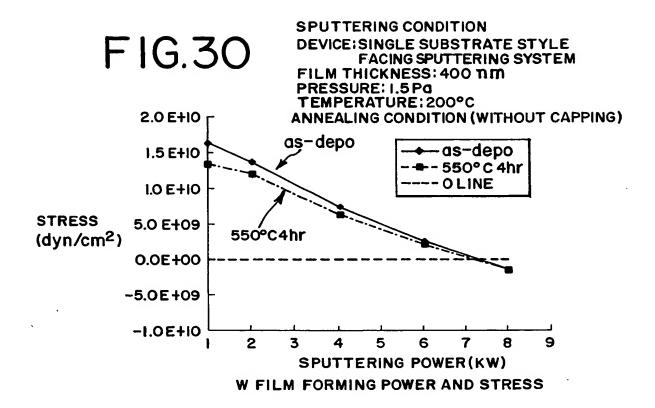
FIG. 29

THE NUMBER OF CONTACT HOLE: 50 CONTACT SURFACE AREA: 20 x 21 μm

62: ELECTRODE (AI-SI)

61: ELECTRODE (WN/W OR TON/TO)

60: SUBSTRATE



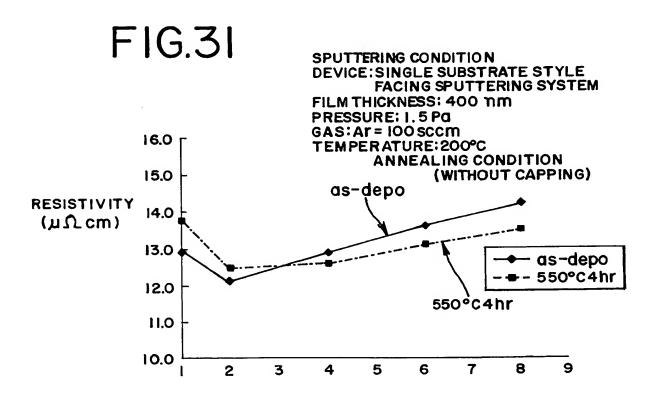


FIG.32

